

L Number	Hits	Search Text	DB	Time stamp
-	3988963	rt a or rtp or anneal\$5 or heat\$4 or (thermal\$3 adj4 treat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/30 21:11
-	71503	cell near5 current	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/30 16:53
-	25935	(rt a or rtp or anneal\$5 or heat\$4 or (thermal\$3 adj4 treat\$5)) and (cell near5 current)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/30 16:54
-	121947	(bit or gate) adj3 line	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/30 16:54
-	2233	((rt a or rtp or anneal\$5 or heat\$4 or (thermal\$3 adj4 treat\$5)) and (cell near5 current)) and ((bit or gate) adj3 line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/30 16:55
-	1365080	implant\$5 or inject\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/30 16:55
-	1641	((rt a or rtp or anneal\$5 or heat\$4 or (thermal\$3 adj4 treat\$5)) and (cell near5 current)) and ((bit or gate) adj3 line)) and (implant\$5 or inject\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/30 16:57
-	1534161	memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/30 16:57
-	1578	((rt a or rtp or anneal\$5 or heat\$4 or (thermal\$3 adj4 treat\$5)) and (cell near5 current)) and ((bit or gate) adj3 line)) and (implant\$5 or inject\$5)) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/30 21:09
-	4509	(rt a or rtp or anneal\$5 or heat\$4 or (thermal\$3 adj4 treat\$5)) same (cell near5 current)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/30 16:58
-	517791	plug	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/30 16:58
-	46666	(implant\$5 or inject\$5) same ((bit or gate) adj3 line) or plug)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/30 16:59
-	76	((rt a or rtp or anneal\$5 or heat\$4 or (thermal\$3 adj4 treat\$5)) same (cell near5 current)) and ((implant\$5 or inject\$5) same ((bit or gate) adj3 line) or plug)) and (rt a or rtp or anneal\$5 or heat\$4 or (thermal\$3 adj4 treat\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/30 17:04

-	43	((rta or rtp or anneal\$5 or heat\$4 or (thermal\$3 adj4 treat\$5)) same (cell near5 current)) and ((implant\$5 or inject\$5) same ((bit or gate) adj3 line) or plug)) and (rta or rtp or anneal\$5 or heat\$4 or (thermal\$3 adj4 treat\$5))) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/30 17:42
-	567906	poly or poly\$lsi or poly\$lsilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/30 17:58
-	33198	(poly or poly\$lsi or poly\$lsilicon) with (plug or contact\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/30 17:44
-	391714	eprom or non\$volatile or flash	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/30 17:45
-	5430	(implant\$5 or inject\$5) same ((poly or poly\$lsi or poly\$lsilicon) with (plug or contact\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/30 17:45
-	390	((implant\$5 or inject\$5) same ((poly or poly\$lsi or poly\$lsilicon) with (plug or contact\$3))) and (rta or rtp or anneal\$5 or heat\$4 or (thermal\$3 adj4 treat\$5)) and (eprom or non\$volatile or flash)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/30 17:46
-	643361	polycrystal\$4 or (poly or poly\$lsi or poly\$lsilicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/30 17:59
-	176495	(source or drain or bit) adj6 (electrode or contact)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/30 18:00
-	6519	implant\$6 with ((source or drain or bit) adj6 (electrode or contact))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/30 18:01
-	1265	(rta or rtp or anneal\$5 or heat\$4 or (thermal\$3 adj4 treat\$5)) same (implant\$6 with ((source or drain or bit) adj6 (electrode or contact)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/30 18:01
-	110	((rta or rtp or anneal\$5 or heat\$4 or (thermal\$3 adj4 treat\$5)) same (implant\$6 with ((source or drain or bit) adj6 (electrode or contact)))) and (eprom or non\$volatile or flash)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/30 18:28
-	12	("6596632") or ("6284581") or ("6277739") or ("6051487") or ("5970331") or ("5554565")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/30 18:29
-	405	438/532.ccls. or 438/533.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/30 21:09
-	3988963	rta or rtp or anneal\$5 or heat\$4 or (thermal\$3 adj4 treat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/30 22:32

-	311	(438/532.ccls. or 438/533.ccls.) and (rta or rtp or anneal\$5 or heat\$4 or (thermal\$3 adj4 treat\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/30 22:31
-	184	(rta or rapid adj5 anneal\$5) with diffusi\$4 with (source or drain)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/30 23:29
-	339	(rta or rapid adj5 anneal\$5) same ramp\$4	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/30 23:29